

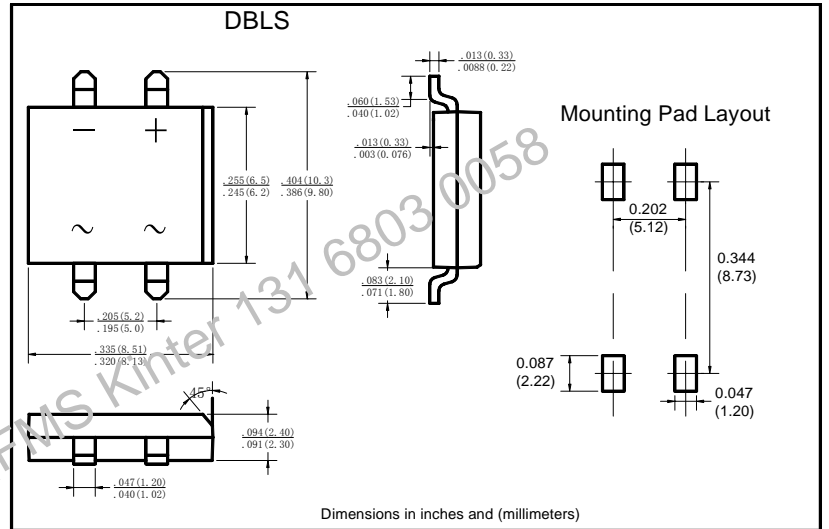
■ Features

- I_o 2A
- V_{RRM} 50V~1000V
- 玻璃钝化芯片
Glass passivated chip
- 耐正向浪涌电流能力高
High surge forward current capability

■ Applications

- 作一般电源单相桥式整流用
General purpose 1 phase Bridge rectifier applications

■ Outline Dimensions and Mark



■ Limiting Values (Absolute Maximum Rating)

参数名称 Item	符号 Symbol	单位 Unit	条件 Conditions	DBL2						
				01S	02S	03S	04S	05S	06S	07S
反向重复峰值电压 Repetitive Peak Reverse Voltage	V_{RRM}	V		50	100	200	400	600	800	1000
平均整流输出电流 Average Rectified Output Current	I_o	A	60Hz正弦波, 电阻负载, $T_a=25^\circ C$ 60Hz sine wave, R-load, $T_a=25^\circ C$ 安装在玻璃-环氧基板上 On glass-epoxi substrate	2.0						
正向(不重复)浪涌电流 Surge(Non-repetitive)Forward Current	I_{FSM}	A	60Hz正弦波, 一个周期, $T_j=25^\circ C$ 60Hz sine wave, 1 cycle, $T_j=25^\circ C$	60						
正向浪涌电流的平方对电流浪涌持续时间的积分值 Current Squared Time	I^2t	A ² S	1ms ≤ t < 8.3ms $T_j=25^\circ C$, 单个二极管 1ms ≤ t < 8.3ms $T_j=25^\circ C$, Rating of per diode	15						
存储温度 Storage Temperature	T_{stg}	°C		-55 ~ +150						
结温 Junction Temperature	T_j	°C		-55 ~ +150						

■ Electrical Characteristics ($T_a=25^\circ C$ Unless otherwise specified)

参数名称 Item	符号 Symbol	单位 Unit	测试条件 Test Condition	最大值 Max
正向峰值电压 Peak Forward Voltage	V_{FM}	V	$I_{FM}=2.0A$, 脉冲测试, 单个二极管的额定值 $I_{FM}=2.0A$, Pulse measurement, Rating of per diode	1.1
反向峰值电流 Peak Reverse Current	I_{RRM}	μA	$V_{RM}=V_{RRM}$, 脉冲测试, 单个二极管的额定值 $V_{RM}=V_{RRM}$, Pulse measurement, Rating of per diode	10
热阻 Thermal Resistance	$R_{\theta J-A}$	°C/W	结和环境之间, 安装在玻璃-环氧基板上 Between junction and ambient, On glass-epoxi substrate	68
	$R_{\theta J-L}$		结和引线之间 Between junction and lead	15

■ Characteristics(Typical)

图1: Io-Ta曲线
FIG1:Io-Ta Curve

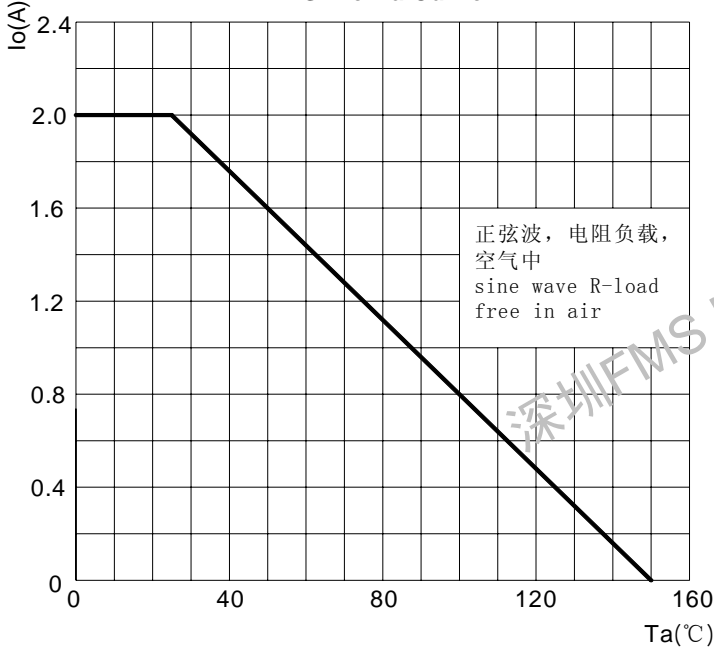


图2: 耐正向浪涌电流曲线
FIG2: Surge Forward Current Capability

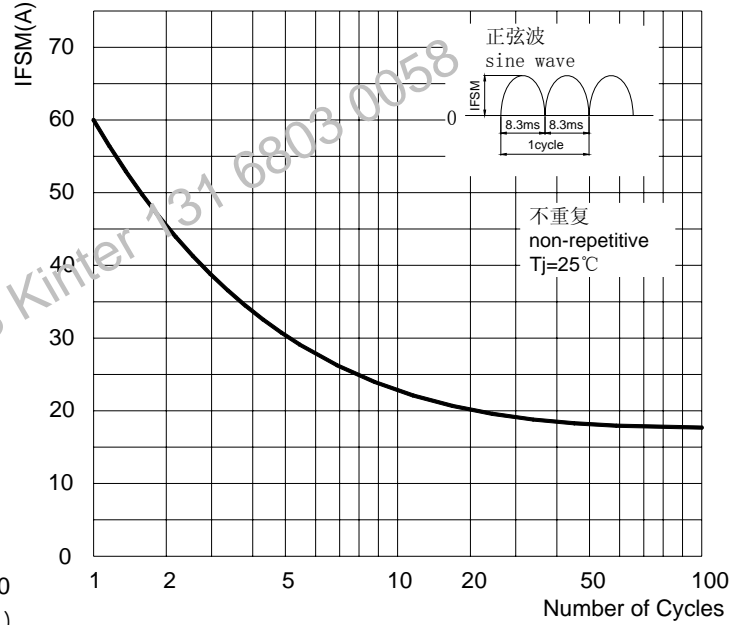


图3: 正向电压曲线
FIG3: Forward Voltage

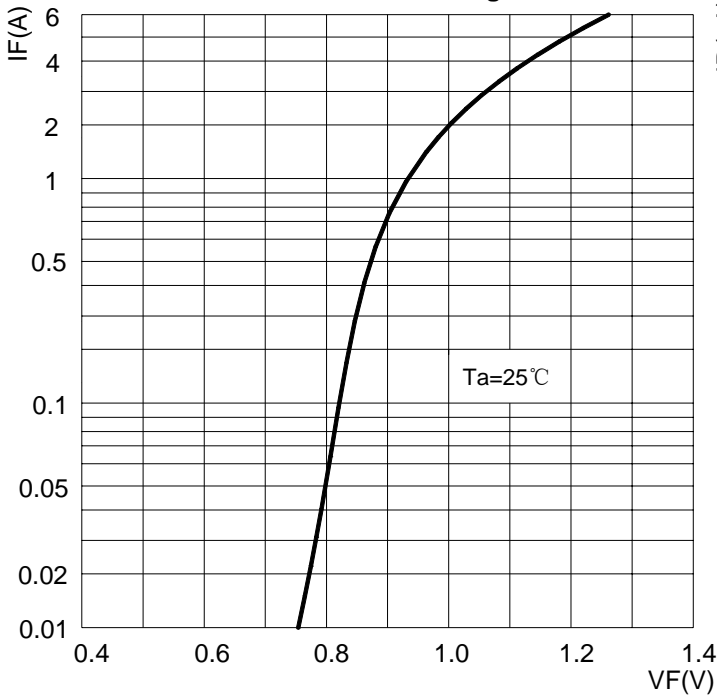


图4: 反向电流曲线
FIG4: Typical Reverse Characteristics

